

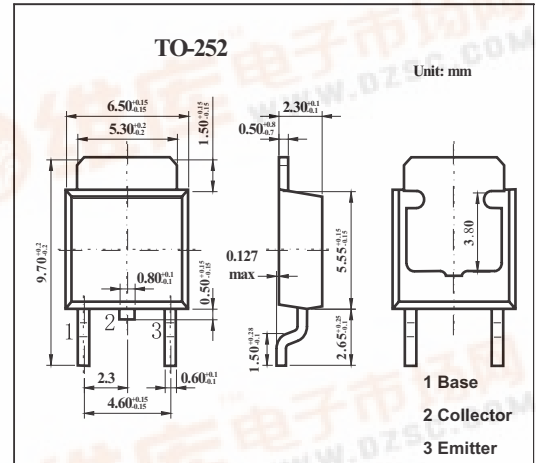
SMD Type Transistors

NPN Epitaxial Silicon Transistor

MJD340

■ Features

- Load Formed for Surface Mount Application
- Straight Lead



■ Absolute Maximum Ratings Ta = 25°C unless otherwise noted

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	300	V
Collector-Emitter Voltage	V _{CEO}	300	V
Emitter-Base Voltage	V _{EBO}	3	V
Collector Current (DC)	I _C	0.5	A
Collector Current (Pulse)	I _{CP}	0.75	A
Collector Dissipation (TC = 25°C)	P _C	15	A
Collector Dissipation (Ta = 25°C)		1.56	W
Junction Temperature	T _J	150	W
Storage Temperature	T _{STG}	-65 to 150	°C

■ Electrical Characteristics Ta = 25°C unless otherwise noted

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-Emitter Sustaining Voltage *	V _{CEO(sus)}	I _C = 1mA, I _B = 0	300			V
Collector Cut-off Current	I _{CEO}	V _{CB} = 300V, I _E = 0			0.1	mA
Emitter Cut-off Current	I _{EBO}	V _{EB} = 3V, I _C = 0			0.1	mA
DC Current Gain *	h _{FE}	V _{CE} = 10V, I _C = 50mA	30		240	

*Pulse Test: PW ≤ 300μs, Duty Cycle ≤ 2%

